

**P-CHANNEL MOS FIELD EFFECT TRANSISTOR  
FOR SWITCHING**

**DESCRIPTION**

The μPA1910 is a switching device which can be driven directly by a 2.5-V power source.

The μPA1910 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

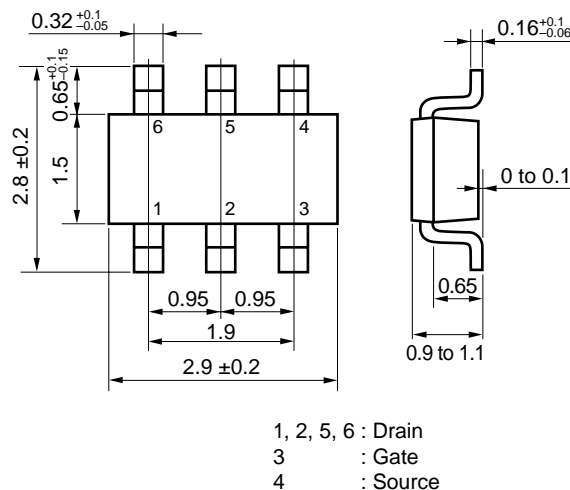
**FEATURES**

- Can be driven by a 2.5-V power source
- Low on-state resistance  
 $R_{DS(on)1} = 80 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.5 \text{ V, } I_D = -1.5 \text{ A)}$   
 $R_{DS(on)2} = 90 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.0 \text{ V, } I_D = -1.5 \text{ A)}$   
 $R_{DS(on)3} = 100 \text{ m}\Omega \text{ MAX. (} V_{GS} = -3.0 \text{ V, } I_D = -1.0 \text{ A)}$   
 $R_{DS(on)4} = 130 \text{ m}\Omega \text{ MAX. (} V_{GS} = -2.5 \text{ V, } I_D = -1.0 \text{ A)}$

★ **ORDERING INFORMATION**

PART NUMBER	PACKAGE
μPA1910TE	6-pin Mini Mold (Thin Type)

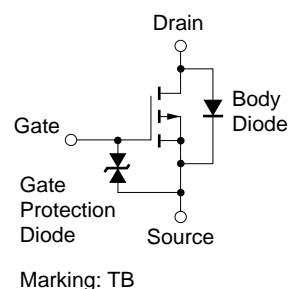
**PACKAGE DRAWING (Unit : mm)**



**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C)**

Drain to Source Voltage	V <sub>DSS</sub>	-12	V
Gate to Source Voltage	V <sub>GSS</sub>	-10/+5	V
Drain Current (DC)	I <sub>D(DC)</sub>	±2.5	A
Drain Current (pulse) <sup>Note1</sup>	I <sub>D(pulse)</sub>	±10	A
★ Total Power Dissipation	P <sub>T1</sub>	0.2	W
Total Power Dissipation <sup>Note2</sup>	P <sub>T2</sub>	2	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**EQUIVALENT CIRCUIT**



- Notes 1.** PW ≤ 10 μs, Duty Cycle ≤ 1 %  
**2.** Mounted on FR-4 board, t ≤ 5 sec.

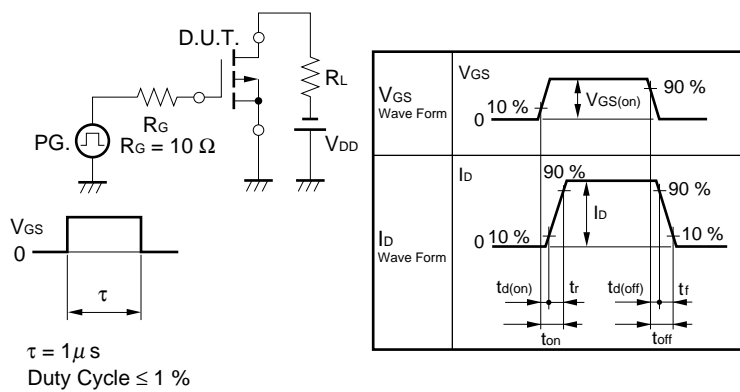
**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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 Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

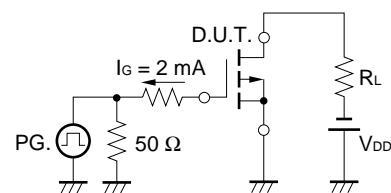
**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)**

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -12 V, V <sub>GS</sub> = 0 V			-10	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±10 V, V <sub>DS</sub> = 0 V			±10	μA
Gate to Source Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA	-0.4	-0.72	-1.5	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1.5 A	1	5.1		S
Drain to Source On-state Resistance	R <sub>DS(on)1</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -1.5 A		60	80	mΩ
	R <sub>DS(on)2</sub>	V <sub>GS</sub> = -4.0 V, I <sub>D</sub> = -1.5 A		63	90	mΩ
	R <sub>DS(on)3</sub>	V <sub>GS</sub> = -3.0 V, I <sub>D</sub> = -1.0 A		75	100	mΩ
	R <sub>DS(on)4</sub>	V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -1.0 A		86	130	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V		386		pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V		283		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1 MHz		154		pF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -10 V		131		ns
Rise Time	t <sub>r</sub>	I <sub>D</sub> = -1.5 A		603		ns
Turn-off Delay Time	t <sub>d(off)</sub>	V <sub>GS(on)</sub> = -4.0 V		427		ns
Fall Time	t <sub>f</sub>	R <sub>G</sub> = 10 Ω		1470		ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DD</sub> = -10 V		6.7		nC
Gate to Source Charge	Q <sub>GS</sub>	I <sub>D</sub> = -3.0 A		1.6		nC
Gate to Drain Charge	Q <sub>GD</sub>	V <sub>GS</sub> = -4.0 V		2.9		nC
Diode Forward Voltage	V <sub>F(S-D)</sub>	I <sub>F</sub> = 2.5 A, V <sub>GS</sub> = 0 V		0.74		V
★ Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.5 A, V <sub>GS</sub> = 0 V		30.0		ns
★ Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 10 A/μs		2.2		nC

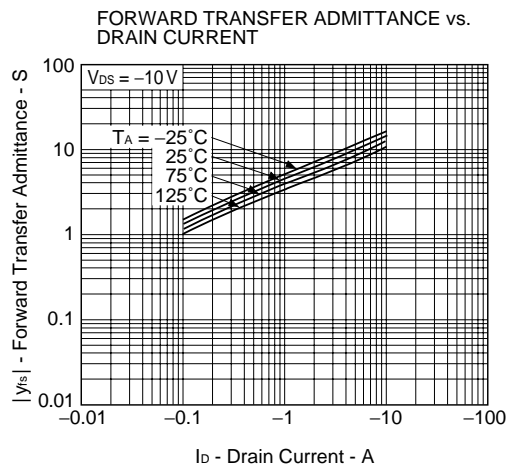
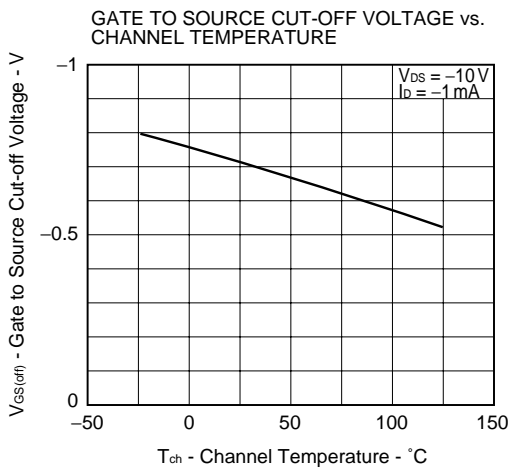
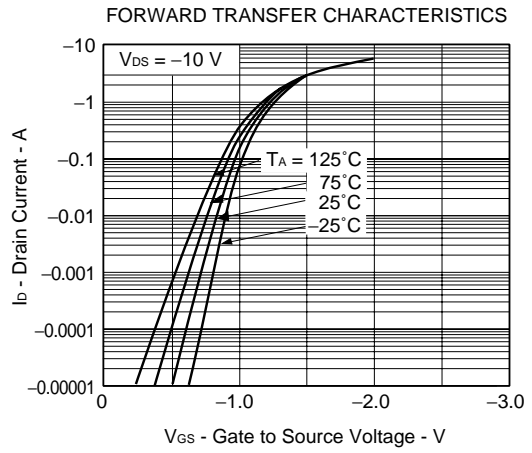
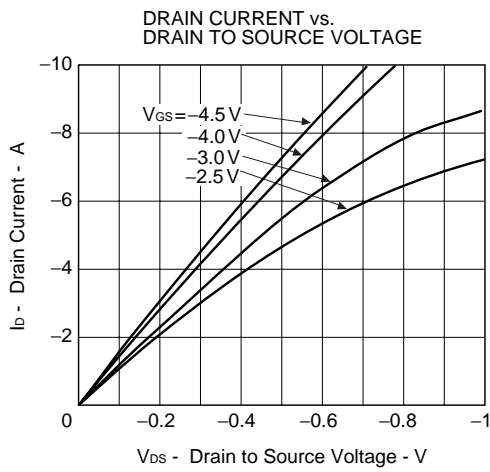
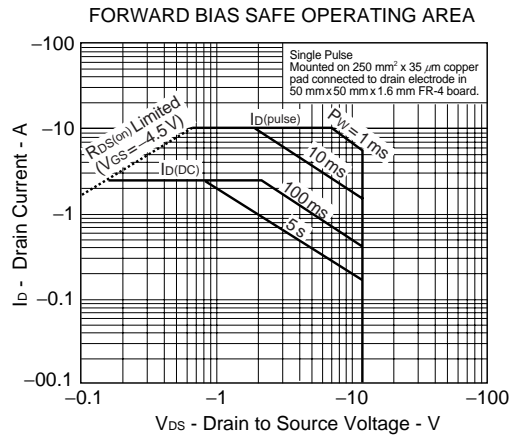
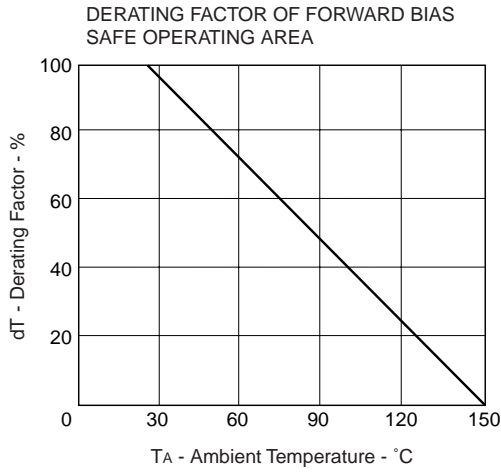
★ **TEST CIRCUIT 1 SWITCHING TIME**

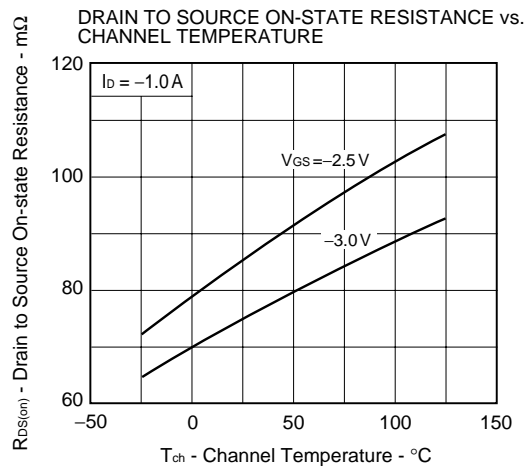
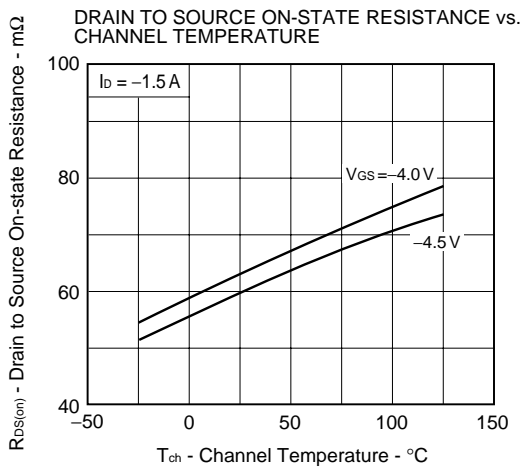
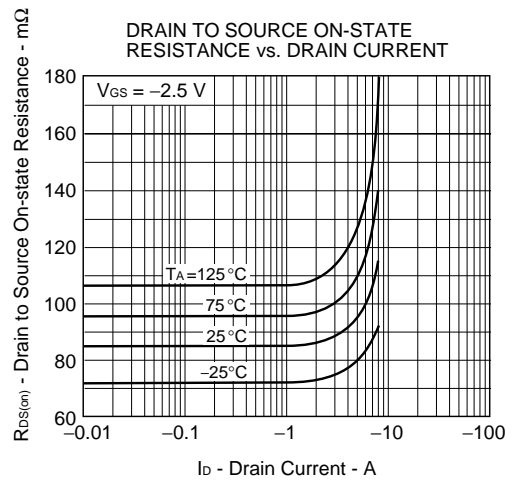
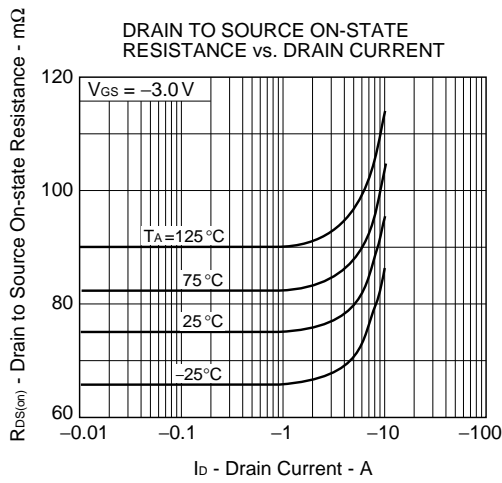
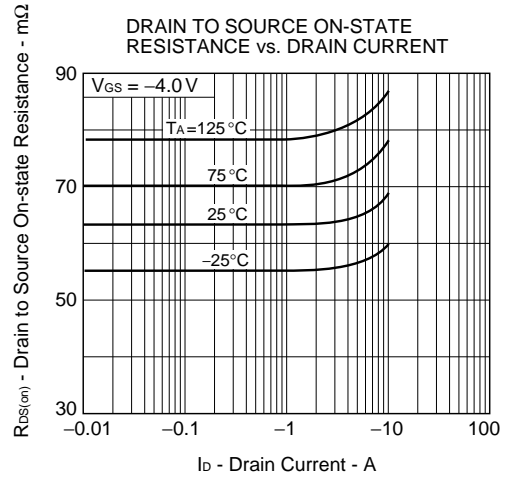
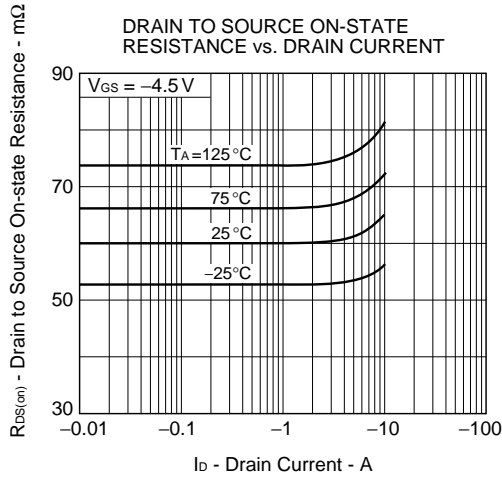


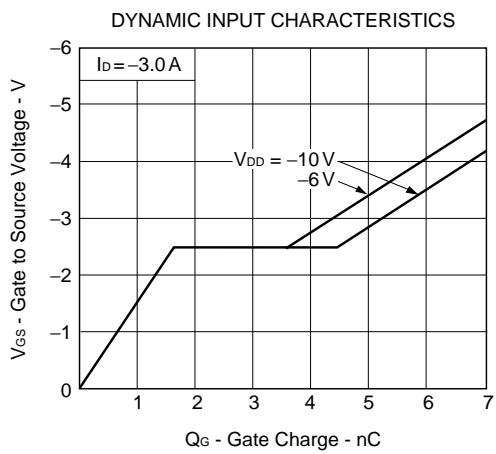
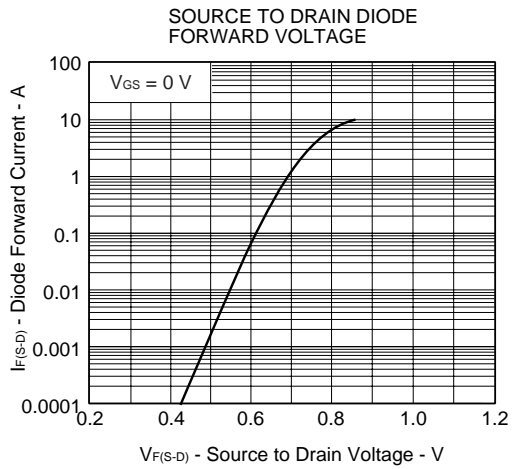
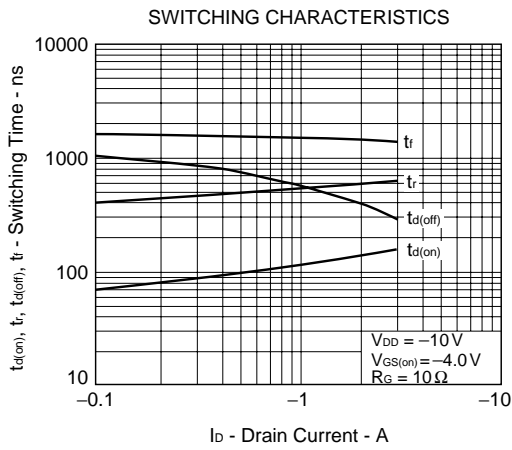
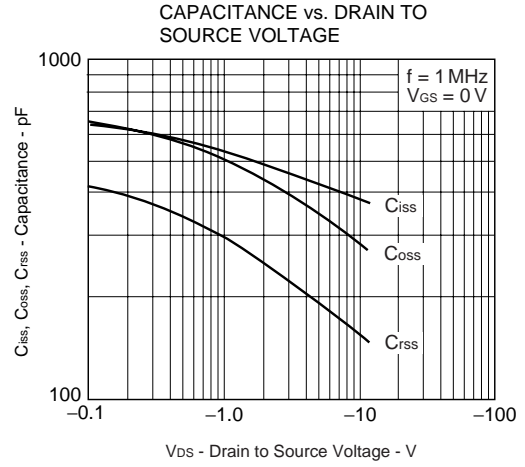
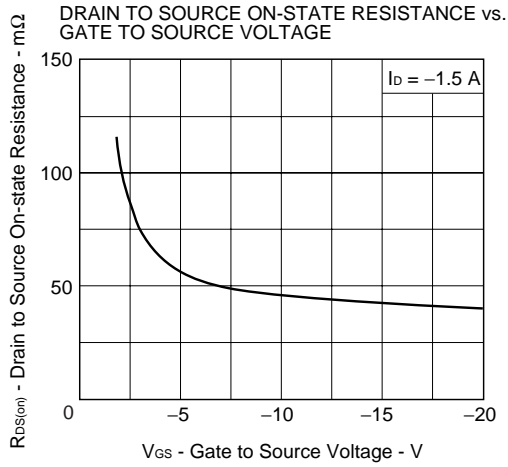
★ **TEST CIRCUIT 2 GATE CHARGE**

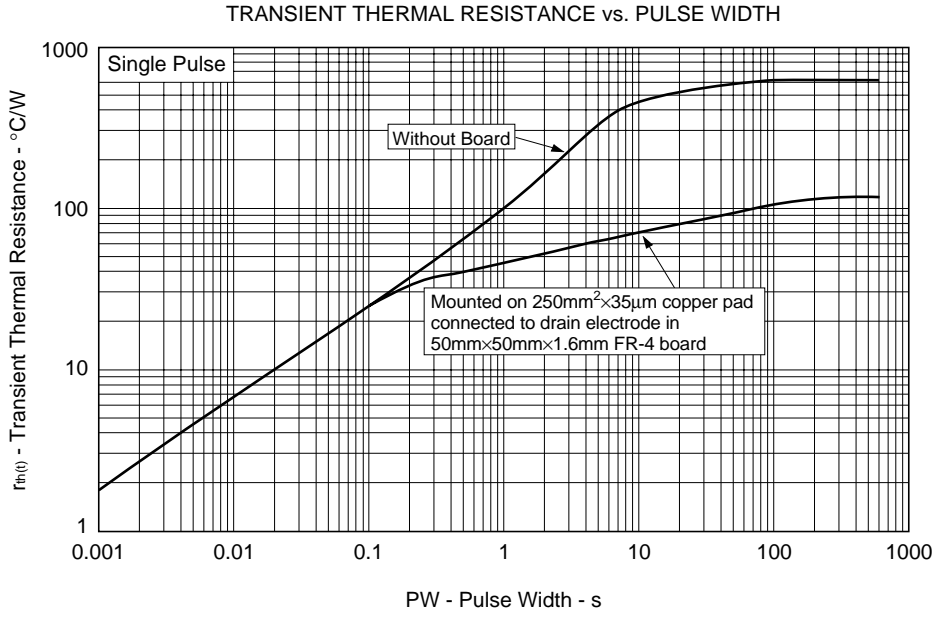


★ TYPICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ )









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